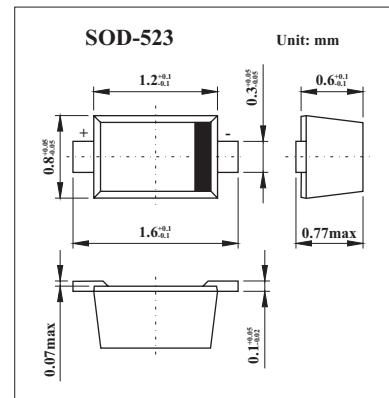


Silicon RF Switching Diode**BAR65-02W****■ Features**

- Low loss, low capacitance PIN-diode
- Band switch for TV-tuners
- Series diode for mobile communication transmit-receiver switch

**■ Absolute Maximum Ratings Ta = 25 °C**

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	30	V
Forward current	I _F	100	mA
Operating temperature range	T _{op}	-55 to +125	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	V _R	V _R = 20 V			20	nA
Forward voltage	V _F	I _F = 100 mA		0.93	1	V
Diode capacitance	C _T	V _R = 1 V, f = 1 MHz		0.6	0.9	pF
		V _R = 3 V, f = 1 MHz		0.57	0.8	
Forward resistance	r _f	I _F = 5 mA, f = 100 MHz		0.65	0.95	Ω
		I _F = 10 mA, f = 100 MHz		0.56	0.9	
Series inductance	L _s			0.6		nH

■ Marking

Marking	N
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